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Tech ID: 23311

ADDITIONAL TECHNOLOGIES BY THESE INVENTORS

- ▶ High-Quality N-Face GaN, InN, AlN by MOCVD
- ▶ Defect Reduction in GaN films using in-situ SiNx Nanomask
- ▶ A Structure For Increasing Mobility In A High-Electron-Mobility Transistor
- ▶ Improved Fabrication of Nonpolar InGaN Thin Films, Heterostructures, and Devices
- ▶ Methods for Locally Changing the Electric Field Distribution in Electron Devices
- ▶ Technique for the Nitride Growth of Semipolar Thin Films, Heterostructures, and Semiconductor Devices
- ▶ (In,Ga,Al)N Optoelectronic Devices with Thicker Active Layers for Improved Performance
- ▶ GaN-based Vertical Metal Oxide Semiconductor and Junction Field Effect Transistors
- ▶ Novel Current-Blocking Layer in High-Power Current Aperture Vertical Electron Transistors (CAVETs)
- ▶ III-N Transistor With Stepped Cap Layers
- ▶ III-N Based Material Structures and Circuit Modules Based on Strain Management

